







SN54LVC00A, SN74LVC00A

SCAS279U - JANUARY 1993 - REVISED JULY 2024

SNx4LVC00A Quadruple 2-Input Positive-NAND Gates

1 Features

- ESD protection exceeds JESD 22
 - 2000V Human-Body Model
 - 1000V Charged-Device Model
- SN74LVC00A operates from 1.65V to 3.6V
- SN54LVC00A operates from 2V to 3.6V
- SNx4LVC00A specified from -40°C to +85°C and –40°C to +125°C
- SN54LVC00A specified from -55°C to +125°C
- Inputs accept voltages to 5.5V
- Max t_{pd} of 4.3ns at 3.3V
- Typical V_{OLP} (output ground bounce) < 0.8V at $V_{CC} = 3.3V$, $T_A = 25$ °C
- Typical V_{OHV} (output V_{OH} undershoot) > 2V at V_{CC} = 3.3V, T_A = 25°C
- Latch-up performance exceeds 250 mA per JESD 17
- On products compliant to MIL-PRF-38535, all parameters are tested unless otherwise noted. On all other products, production processing does not necessarily include testing of all parameters.

2 Applications

- **AV Receivers**
- Audio Docks: Portable
- Blu-Ray Players and Home Theater
- MP3 Players or Recorders
- Personal Digital Assistants (PDAs)
- Power: Telecom/Server AC/DC Supply: Single Controller: Analog and Digital
- Solid State Drives (SSDs): Client and Enterprise
- TVs: LCD, Digital, and High-Definition (HDTV)
- Tablets: Enterprise
- Video Analytics: Server
- Wireless Headsets, Keyboards, and Mice

3 Description

The SN54LVC00A quadruple 2-input positive-NAND gate is designed for 2.7V to 3.6V V_{CC} operation, and the SN74LVC00A quadruple 2-input positive-NAND gate is designed for 1.65V to 3.6V V_{CC} operation.

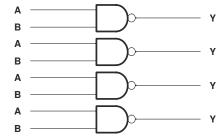
The SNx4LVC00A devices perform the Boolean function $Y = \overline{A \cdot B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

Inputs can be driven from either 3.3V or 5V devices. This feature allows the use of these devices as translators in a mixed 3.3V/5V system environment.

Device Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE(2)	BODY SIZE(3)
	BQA (WQFN, 14)	3mm × 2.5mm	3mm × 2.5mm
	D (SOIC, 14)	8.65mm × 6mm	8.65 mm × 3.91 mm
	DB (SSOP, 14)	6.2mm × 7.8mm	6.20 mm × 5.30 mm
	NS (SOP, 14)	10.2mm × 7.8mm	10.30 mm × 5.30 mm
SNx4LVC00A	PW (TSSOP, 14)	5mm × 4.4mm	5.00 mm × 4.40 mm
	RGY (VQFN, 14)	3.5mm × 3.5mm	3.50 mm × 3.50 mm
	FK (LCCC, 20)	8.9mm x 8.9mm	8.89 mm × 8.89 mm
	J (CDIP, 14)	19.55mm x 7.9mm	19.55 mm x 6.7mm
	W (CFP, 14)	9.21mm x 9mm	9.21mm x 6.28mm

- For more information, see Section 11.
- The package size (length × width) is a nominal value and includes pins, where applicable.
- The body size (length × width) is a nominal value and does not include pins.



Simplified Schematic



Table of Contents

1 Features1	7 Detailed Description9
2 Applications 1	7.1 Overview9
3 Description1	7.2 Functional Block Diagram9
4 Pin Configuration and Functions3	7.3 Feature Description9
5 Specifications4	7.4 Device Functional Modes10
5.1 Absolute Maximum Ratings4	8 Application and Implementation11
5.2 ESD Ratings4	8.1 Application Information11
5.3 Recommended Operating Conditions,	8.2 Typical Application11
SN54LVC00A4	8.3 Layout
5.4 Recommended Operating Conditions,	9 Device and Documentation Support13
SN74LVC00A5	9.1 Related Links13
5.5 Thermal Information5	9.2 Receiving Notification of Documentation Updates13
5.6 Electrical Characteristics, SN54LVC00A6	9.3 Support Resources13
5.7 Electrical Characteristics, SN74LVC00A6	9.4 Trademarks13
5.8 Switching Characteristics, SN54LVC00A6	9.5 Electrostatic Discharge Caution13
5.9 Switching Characteristics, SN74LVC00A7	9.6 Glossary13
5.10 Operating Characteristics7	11 Mechanical, Packaging, and Orderable
5.11 Typical Characteristics7	Information14
6 Parameter Measurement Information8	



4 Pin Configuration and Functions

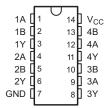
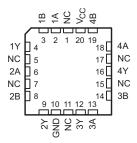


Figure 4-1. SN54LVC00A J or W Package; SN74LVC00A D, DB, NS, or PW Package 14-Pin CDIP, CFP

SOIC, SSOP, SO, or TSSOP (Top View)



NC - No internal connection

Figure 4-2. SN54LVC00A FK Package 20-Pin LCCC (Top View)

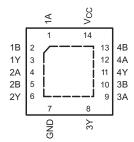


Figure 4-3. SN74LVC00A BQA or RGY Package 14-Pin WQFN or VQFN (Top View)

Table 4-1. Pin Functions

		PIN		1. I III I UIICUO		
NAME	SN74L	VC00A	SN54	LVC00A	TYPE	DESCRIPTION
NAIVIE	D, DB, NS, PW	BQA, RGY	J, W	FK		
1A	1	1	1	2	I	Gate 1 input
1B	2	2	2	3	I	Gate 1 input
1Y	3	3	3	4	0	Gate 1 output
2A	4	4	4	6	I	Gate 2 input
2B	5	5	5	8	I	Gate 2 input
2Y	6	6	6	9	0	Gate 2 output
GND	7	7	7	10	I	Ground Pin
3Y	8	8	8	12	0	Gate 3 output
3A	9	9	9	13	I	Gate 3 input
3B	10	10	10	14	I	Gate 3 input
4Y	11	11	11	16	0	Gate 4 output
4A	12	12	12	18	I	Gate 4 input
4B	13	13	13	19	I	Gate 4 input
V _{CC}	14	14	14	20	_	Positive supply
				1		
				5		
NC				7		No Connection
INC	_	_	_	11	_	INO COMPECTION
				15		
				17		



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	6.5	V
VI	Input voltage ⁽²⁾		-0.5	6.5	V
Vo	Output voltage (2) (3)		-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current	·		±50	mA
V _{CC}	Continuous current through GND			±100	mA
P _{tot}	Power dissipation ^{(4) (5)}	$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		500	mW
T _J	Junction temperature			150	°C
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- (2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The value of V_{CC} is provided in the Recommended Operating Conditions table.
- (4) For the D package: above 70°C, the value of Ptot derates linearly with 8 mW/K.
- (5) For the DB, NS, and PW packages: above 60°C, the value of Ptot derates linearly with 5.5 mW/K.

5.2 ESD Ratings

				VALUE	UNIT
			Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	
V _{(f}	ESD)	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions, SN54LVC00A

over operating free-air temperature range (unless otherwise noted)(1)

			SN54	LVC00A	
			−55°C t	o +125°C	UNIT
			MIN	MAX	
\/	Supply voltage	Operating	2	3.6	V
V _{CC}	Supply voltage	Data retention only	1.5		'
V _{IH}	High-level input voltage	V _{CC} = 2.7 V to 3.6 V	2		V
V _{IL}	Low-level input voltage	V _{CC} = 2.7 V to 3.6 V		0.8	V
VI	Input voltage		0	5.5	V
Vo	Output voltage		0	V _{CC}	V
	High-level output current	V _{CC} = 2.7 V		-12	mA
I _{OH}	nigh-level output current	V _{CC} = 3 V		-24	IIIA
	Low level output ourrent	V _{CC} = 2.7 V		12	m A
I _{OL}	Low-level output current	V _{CC} = 3 V		24	· mA

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See *Implications of Slow or Floating CMOS Inputs*, SCBA004.

Submit Document Feedback



5.4 Recommended Operating Conditions, SN74LVC00A

over operating free-air temperature range (unless otherwise noted)(1)

	-				SN74L	VC00A				
			T _A =	25°C	-40°C 1	o 85°C	–40°C to	125°C	UNIT	
			MIN	MAX	MIN	MAX	MIN	MAX		
V	Supply voltage	Operating	1.65	3.6	1.65	3.6	1.65	3.6	V	
V _{CC}	Supply voltage	Data retention only	1.5		1.5		1.5		V	
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		0.65 × V _{CC}		0.65 × V _{CC}			
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		1.7		1.7		V	
	par ronago	V _{CC} = 2.7 V to 3.6 V	2		2		2			
	Lowleyel	V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}		0.35 × V _{CC}		0.35 × V _{CC}		
V _{IL}	Low-level input voltage	V _{CC} = 2.3 V to 2.7 V		0.7		0.7		0.7	V	
	par remage	V _{CC} = 2.7 V to 3.6 V		0.8		0.8		0.8		
VI	Input voltage		0	5.5	0	5.5	0	5.5	V	
Vo	Output voltage		0	V _{CC}	0	V _{CC}	0	V _{CC}	V	
		V _{CC} = 1.65 V		-4		-4		-4		
	High-level	V _{CC} = 2.3 V		-8		-8		-8	mA	
I _{OH}	output current	V _{CC} = 2.7 V		-12		-12		-12	mA	
		V _{CC} = 3 V		-24		-24		-24		
		V _{CC} = 1.65 V		4		4		4		
	Low-level	V _{CC} = 2.3 V		8		8		8	m A	
I _{OL}	output current	V _{CC} = 2.7 V		12		12		12	mA	
		V _{CC} = 3 V		24		24		24		

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See *Implications of Slow or Floating CMOS Inputs*, SCBA004.

5.5 Thermal Information

		SN74LVC00A						
	THERMAL METRIC ⁽¹⁾	BQA (WQFN)	D (SOIC)	O (SOIC) DB (SSOP)		PW (TSSOP)	RGY (VQFN)	UNIT
			14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	102.3	127.8	140.4	123.8	150.8	92.1	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

5.6 Electrical Characteristics, SN54LVC00A

over recommended operating free-air temperature range (unless otherwise noted)

			SN54LV0	C00A		
PARAMETER	TEST CONDITIONS	V _{cc}	-55°C to +	125°C	UNIT	
			MIN	MAX		
	$I_{OH} = -100 \mu A$	2.7 V to 3.6 V	V _{CC} - 0.2			
V_{OH}	I _{OH} = –12 mA	2.7 V	2.2			
	10H 12 IIIA	3 V	2.4		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
	$I_{OH} = -24 \text{ mA}$	3 V	2.2			
	Ι _{ΟL} = 100 μΑ	2.7 V to 3.6 V		0.2		
V _{OL}	I _{OL} = 12 mA	2.7 V		0.4	V	
	I _{OL} = 24 mA	3 V		0.55		
I _I	V _I = 5.5 V or GND	3.6 V		±5	μA	
I _{CC}	$V_I = V_{CC}$ or GND, $I_O = 0$	3.6 V		10	μA	
ΔI_{CC}	One input at $V_{CC} - 0.6 \text{ V}$, Other inputs at V_{CC} or GND	2.7 V to 3.6 V		500	μA	

5.7 Electrical Characteristics, SN74LVC00A

over recommended operating free-air temperature range (unless otherwise noted)

					:	SN74LVC00A				
PARAMETER	TEST CONDITIONS	V _{cc}	T _A =	= 25°C		-40°C to +8	35°C	-40°C to +1	25°C	UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
	I _{OH} = -100 μA	1.65 V to 3.6 V	V _{CC} - 0.2			V _{CC} - 0.2		V _{CC} - 0.3		
	I _{OH} = -4 mA	1.65 V	1.29			1.2		1.05		
\	I _{OH} = -8 mA	2.3 V	1.9			1.7		1.55		V
V _{OH}	I _{OH} = -12 mA	2.7 V	2.2			2.2		2.05		v
	10H12 IIIA	3 V	2.4			2.4		2.25		
	I _{OH} = -24 mA	3 V	2.3			2.2		2		
	I _{OL} = 100 μA	1.65 V to 3.6 V			0.1		0.2	·	0.3	
	I _{OL} = 4 mA	1.65 V			0.24		0.45	·	0.6	
V _{OL}	I _{OL} = 8 mA	2.3 V			0.3		0.7	·	0.85	V
	I _{OL} = 12 mA	2.7 V			0.4		0.4		0.6	
	I _{OL} = 24 mA	3 V			0.55		0.55	·	0.8	
I _I	V _I = 5.5 V or GND	3.6 V			±1		±5	·	±20	μΑ
I _{cc}	$V_I = V_{CC}$ or GND, $I_O = 0$	3.6 V			1		10		40	μΑ
ΔI _{CC}	One input at V _{CC} - 0.6 V, Other inputs at V _{CC} or GND	2.7 V to 3.6 V			500		500		5000	μA
Ci	V _I = V _{CC} or GND	3.3 V		5						pF

5.8 Switching Characteristics, SN54LVC00A

over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

					SN54L	VC00A		
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{cc}	−55°C to	UNIT			
		((33.1.3.1)		MIN	MAX		
	t _{pd} A or B	V	2.7 V		5.1	ns		
		AUID	ľ	3.3 V ± 0.3 V	1	4.3	113	

Submit Document Feedback

Copyright © 2024 Texas Instruments Incorporated



5.9 Switching Characteristics, SN74LVC00A

over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

		TO (OUTPUT)	V _{cc}	SN74LVC00A							
PARAMETER	FROM (INPUT)			T _A = 25°C		-40°C to +85°C		-40°C to	+125°C	UNIT	
	(MIN	TYP	MAX	MIN	MAX	MIN	MAX	
	A D	V	1.8 V ± 0.15 V	1	6	12	1	12.5	1	14	
			2.5 V ± 0.2 V	1	4.6	5.9	1	6.4	1	7.9	
t _{pd}	A or B	T	2.7 V	1	4.3	4.9	1	5.1	1	6.5	ns
			3.3 V ± 0.3 V	1	3.5	4.1	1	4.3	1	5.5	
t _{sk(o)}			3.3 V ± 0.3 V					1		1.5	ns

5.10 Operating Characteristics

 $T_A = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS	V _{cc}	TYP	UNIT
			1.8 V	18	
C _{pd}	Power dissipation capacitance per gate	f = 10 MHz	2.5 V	18	pF
			3.3 V	19	

5.11 Typical Characteristics

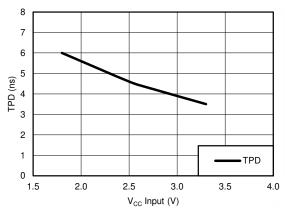
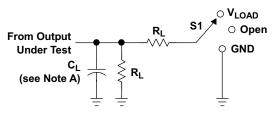


Figure 5-1. TPD vs V_{CC} ($T_A = 25^{\circ}C$)



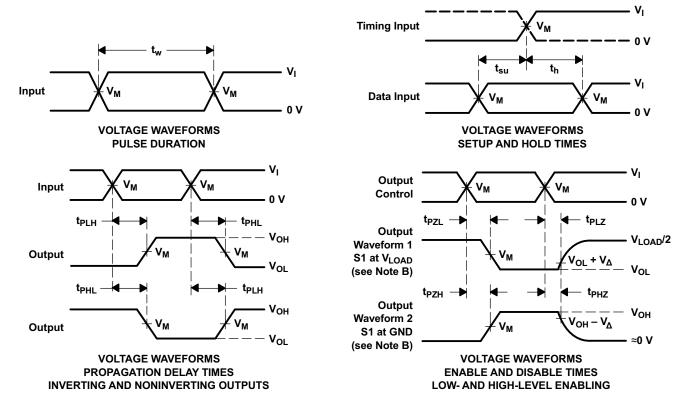
6 Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LO	AD	CIR	Cι	JIT

.,	INF	PUTS	.,	.,		_	,,
V _{CC}	VI	t _r /t _f	V _M	V _{LOAD}	CL	R_L	V _A
1.8 V ± 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	2 × V _{CC}	30 pF	1 kΩ	0.15 V
2.5 V ± 0.2 V	V _{CC}	≤2 ns	V _{CC} /2	2 × V _{CC}	30 pF	500 Ω	0.15 V
2.7 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
3.3 V ± 0.3 V	2.7 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 6-1. Load Circuit and Voltage Waveforms



7 Detailed Description

7.1 Overview

The maximum sink and source current is 24 mA.

Inputs can be driven from 1.8-V, 2.5-V, 3.3-V (LVTTL), or 5-V (CMOS) devices. This feature allows the use of this device as translators in a mixed-system environment.

7.2 Functional Block Diagram



Figure 7-1. Logic Diagram, Each Gate (Positive Logic)

7.3 Feature Description

7.3.1 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the power output of the device to be limited to avoid thermal runaway and damage due to over-current. The electrical and thermal limits defined the in the Section 5.1 must be followed at all times.

7.3.2 Standard CMOS Inputs

Standard CMOS inputs are high impedance and are typically modelled as a resistor in parallel with the input capacitance given in the Section 5.6 and Section 5.7. The worst case resistance is calculated with the maximum input voltage, given in the Section 5.1, and the maximum input leakage current, given in the Section 5.6 and Section 5.7, using ohm's law ($R = V \div I$).

Signals applied to the inputs need to have fast edge rates, as defined by $\Delta t/\Delta v$ in Section 5.3 and Section 5.4 to avoid excessive currents and oscillations. If a slow or noisy input signal is required, a device with a Schmitt-trigger input should be utilized to condition the input signal prior to the standard CMOS input.

7.3.3 Clamp Diodes

The inputs and outputs to this device have negative clamping diodes.

CAUTION

Voltages beyond the values specified in the *Section 5.1* table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

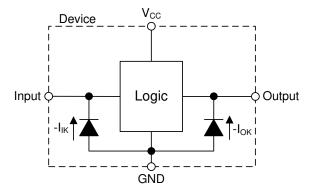


Figure 7-2. Electrical Placement of Clamping Diodes for Each Input and Output



7.3.4 Over-voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage so long as they remain below the maximum input voltage value specified in the *Section 5.1*.

7.4 Device Functional Modes

Table 7-1 lists the functional modes of SN54LVC00A and SN74LVC00A.

Table 7-1. Function Table (Each Gate)

INP	OUTPUT	
Α	В	Y
Н	Н	L
L	Χ	Н
Х	L	Н

Submit Document Feedback

Copyright © 2024 Texas Instruments Incorporated



8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

SN74LVC00A is a high-drive CMOS device that can be used for a multitude of buffer-type functions. It can produce 24 mA of drive current at 3.3 V. Therefore, this device is ideal for driving multiple inputs and for high-speed applications up to 100 MHz. The inputs and outputs are 5.5-V tolerant allowing the device to allowing the device to perform mixed-voltage input down translation. For example the A input can be 3.3 V and the B input can be 5 V, while V_{CC} = 2.5 V and the device will operate properly to output a 2.5 V signal.

8.2 Typical Application

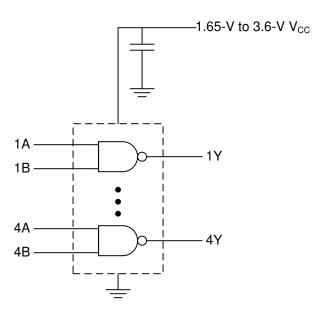


Figure 8-1. Typical NAND Gate Application and Supply Voltage

8.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads; therefore, routing and load conditions should be considered to prevent ringing.

8.2.2 Detailed Design Procedure

- Recommended Input Conditions
 - Rise time and fall time specs: See (Δt/ΔV) in the Section 5.4 table.
 - Specified high and low levels: See (V_{IH} and V_{IL}) in the Section 5.4 table.
 - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC}.
- 2. Recommended Output Conditions
 - Load currents should not exceed 25 mA per output and 50 mA total for the part.
 - Outputs should not be pulled above 5.5 V.

8.2.3 Application Curve

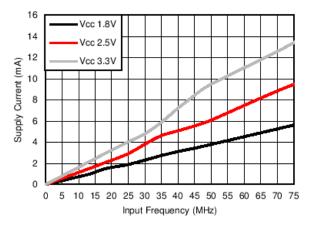


Figure 8-2. I_{CC} vs Frequency

Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the *Section 5.4* table.

Each V_{CC} pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1 μ F is recommended; if there are multiple V_{CC} pins, then 0.01 μ F or 0.022 μ F is recommended for each power pin. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. A 0.1 μ F and a 1 μ F are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

8.3 Layout

8.3.1 Layout Guidelines

When using multiple bit logic devices inputs should never float.

In many cases, functions or parts of functions of digital logic devices are unused, for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Section 8.3.2 specifies the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC} , whichever makes more sense or is more convenient. It is generally acceptable to float outputs, unless the part is a transceiver.

8.3.2 Layout Example

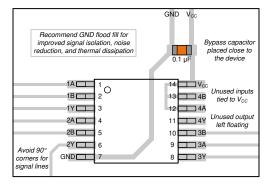


Figure 8-3. Layout Diagram for the SNx4LVC00A



9 Device and Documentation Support

9.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to order now.

Table 9-1. Related Links

PARTS	PRODUCT FOLDER	ORDER NOW	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
SN54LVC00A	Click here	Click here	Click here	Click here	Click here
SN74LVC00A	Click here	Click here	Click here	Click here	Click here

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

9.3.1 Community Resources

9.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

10

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision T (May 2024) to Revision U (July 2024)	Page
•	Updated RθJA values: D = 86 to 127.8, all values in °C/W	5
•	Added Typical Characteristics	7

Changes from Revision S (March 2024) to Revision T (May 2024)

Page

Updated RθJA values: DB = 96 to 140.4, NS = 76 to 123.8, PW = 113 to 150.8, RGY = 47 to 92.1; Updated DB, NS, PW, and RGY packages for RθJC(top), RθJB, ΨJT, ΨJB, and RθJC(bot), all values in °C/W.............5



11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.





www.ti.com 2-Dec-2024

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
5962-9753301Q2A	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962- 9753301Q2A SNJ54LVC 00AFK	Samples
5962-9753301QCA	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753301QC A SNJ54LVC00AJ	Samples
5962-9753301QDA	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753301QD A SNJ54LVC00AW	Samples
5962-9753301VDA	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753301VD A SNV54LVC00AW	Samples
SN74LVC00ABQAR	ACTIVE	WQFN	BQA	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00AD	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00ADBR	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00ADBRG4	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00ADE4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00ADR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00ADRG4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00ADT	ACTIVE	SOIC	D	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00ANSR	ACTIVE	SOP	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00ANSRG4	ACTIVE	SOP	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVC00A	Samples
SN74LVC00APW	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00APWE4	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00APWG4	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples



PACKAGE OPTION ADDENDUM

www.ti.com 2-Dec-2024

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC00APWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00APWRE4	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00APWRG4	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00APWT	ACTIVE	TSSOP	PW	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC00A	Samples
SN74LVC00ARGYR	ACTIVE	VQFN	RGY	14	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LC00A	Samples
SNJ54LVC00AFK	ACTIVE	LCCC	FK	20	55	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962- 9753301Q2A SNJ54LVC 00AFK	Samples
SNJ54LVC00AJ	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753301QC A SNJ54LVC00AJ	Samples
SNJ54LVC00AW	ACTIVE	CFP	W	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-9753301QD A SNJ54LVC00AW	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

PACKAGE OPTION ADDENDUM

www.ti.com 2-Dec-2024

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN54LVC00A, SN54LVC00A-SP, SN74LVC00A:

Catalog: SN74LVC00A, SN54LVC00A

Automotive: SN74LVC00A-Q1, SN74LVC00A-Q1

Enhanced Product: SN74LVC00A-EP, SN74LVC00A-EP

Military: SN54LVC00A

Space: SN54LVC00A-SP

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product Supports Defense, Aerospace and Medical Applications
- Military QML certified for Military and Defense Applications
- Space Radiation tolerant, ceramic packaging and qualified for use in Space-based application



www.ti.com 7-Dec-2024

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC00ABQAR	WQFN	BQA	14	3000	180.0	12.4	2.8	3.3	1.1	4.0	12.0	Q1
SN74LVC00ADBR	SSOP	DB	14	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN74LVC00ADR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74LVC00ADT	SOIC	D	14	250	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74LVC00ANSR	SOP	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
SN74LVC00APWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LVC00APWRG4	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LVC00APWT	TSSOP	PW	14	250	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LVC00ARGYR	VQFN	RGY	14	3000	330.0	12.4	3.75	3.75	1.15	8.0	12.0	Q1



www.ti.com 7-Dec-2024



*All dimensions are nominal

7 til dillicilololio die Hollillai							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC00ABQAR	WQFN	BQA	14	3000	210.0	185.0	35.0
SN74LVC00ADBR	SSOP	DB	14	2000	356.0	356.0	35.0
SN74LVC00ADR	SOIC	D	14	2500	353.0	353.0	32.0
SN74LVC00ADT	SOIC	D	14	250	210.0	185.0	35.0
SN74LVC00ANSR	SOP	NS	14	2000	356.0	356.0	35.0
SN74LVC00APWR	TSSOP	PW	14	2000	356.0	356.0	35.0
SN74LVC00APWRG4	TSSOP	PW	14	2000	356.0	356.0	35.0
SN74LVC00APWT	TSSOP	PW	14	250	356.0	356.0	35.0
SN74LVC00ARGYR	VQFN	RGY	14	3000	356.0	356.0	35.0

PACKAGE MATERIALS INFORMATION



TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
5962-9753301Q2A	FK	LCCC	20	55	506.98	12.06	2030	NA
5962-9753301QDA	W	CFP	14	25	506.98	26.16	6220	NA
5962-9753301VDA	W	CFP	14	25	506.98	26.16	6220	NA
SN74LVC00AD	D	SOIC	14	50	506.6	8	3940	4.32
SN74LVC00ADE4	D	SOIC	14	50	506.6	8	3940	4.32
SN74LVC00APW	PW	TSSOP	14	90	530	10.2	3600	3.5
SN74LVC00APWE4	PW	TSSOP	14	90	530	10.2	3600	3.5
SN74LVC00APWG4	PW	TSSOP	14	90	530	10.2	3600	3.5
SNJ54LVC00AFK	FK	LCCC	20	55	506.98	12.06	2030	NA
SNJ54LVC00AW	W	CFP	14	25	506.98	26.16	6220	NA



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
- 5. Reference JEDEC registration MS-012, variation AB.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No-Lead) package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
- G. Package complies to JEDEC MO-241 variation BA.



RGY (S-PVQFN-N14)

PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

Exposed Thermal Pad Dimensions

4206353-2/P 03/14

NOTE: All linear dimensions are in millimeters



RGY (S-PVQFN-N14)

PLASTIC QUAD FLATPACK NO-LEAD



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com http://www.ti.com.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.



2.5 x 3, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



INSTRUMENTS www.ti.com

PLASTIC QUAD FLAT PACK-NO LEAD



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



PLASTIC QUAD FLAT PACK-NO LEAD



NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLAT PACK-NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

MECHANICAL DATA

NS (R-PDSO-G**)

14-PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



8.89 x 8.89, 1.27 mm pitch

LEADLESS CERAMIC CHIP CARRIER

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



CERAMIC DUAL IN LINE PACKAGE



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4040083-5/G





CERAMIC DUAL IN LINE PACKAGE



NOTES:

- 1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This package is hermitically sealed with a ceramic lid using glass frit.
- His package is remitted by sealed with a ceramic its using glass mit.
 Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
 Falls within MIL-STD-1835 and GDIP1-T14.



CERAMIC DUAL IN LINE PACKAGE







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



W (R-GDFP-F14)

CERAMIC DUAL FLATPACK



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only.
- E. Falls within MIL STD 1835 GDFP1-F14







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-150.





NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2024, Texas Instruments Incorporated